

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-20 (Canceled).

Claim 21 (Previously Presented): A semiconductor device comprising:

a first semiconductor layer formed on a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said first semiconductor layer, said first semiconductor layer having a shape different than a rectangle; and

a second semiconductor layer having a rim portion formed on an outerperipheral of said semiconductor substrate, said rim portion of said second semiconductor layer surrounding said first semiconductor layer, said second semiconductor layer further having a rectangular portion, and said rectangular portion of said second semiconductor layer and said first semiconductor layer having together the shape of a rectangle.

Claim 22 (Original): A semiconductor device according to claim 21, wherein the area of said second semiconductor layer is larger than the area of said first semiconductor layer.

Claim 23 (Original): A semiconductor device according to claim 21, wherein said second semiconductor layer is deposited by epitaxial growth.

Claim 24 (Canceled).

Claim 25 (New): A semiconductor device comprising:

a plurality of first semiconductor layers formed in a first region of a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said plurality of first semiconductor layers; and

a second semiconductor layer formed in a second region of said semiconductor substrate,

wherein each of said plurality of first semiconductor layers is surrounded by said second semiconductor layer, and

said plurality of first semiconductor layers are arranged to be symmetrical with respect to a certain point on said semiconductor substrate, viewed from above a main surface of said semiconductor substrate.

Claim 26 (New): A semiconductor device according to claim 25, wherein logic circuits are formed in said plurality of first semiconductor layers, and at least one of a storage element, an analog element, and a single input/output circuit is formed in said second semiconductor layer.

Claim 27 (New): A semiconductor device according to claim 25, wherein an area of said second semiconductor layer is larger than a sum of the areas of said plurality of first semiconductor layers.

Claim 28 (New): A semiconductor device according to claim 25, wherein said second semiconductor layer is deposited by epitaxial growth.

Claim 29 (New): A semiconductor device comprising:

a plurality of first semiconductor layers formed in a first region of a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said plurality of first semiconductor layers; and

a second semiconductor layer formed in a second region of said semiconductor substrate,

wherein each of said plurality of first semiconductor layers is surrounded by said second semiconductor layer, and

said plurality of first semiconductor layers are arranged to be symmetrical with respect to a certain straight line on said semiconductor substrate, viewed from above a main surface of said semiconductor substrate.

Claim 30 (New): A semiconductor device according to claim 29, wherein logic circuits are formed in said plurality of first semiconductor layers, and at least one of a storage element, an analog element, and a single input/output circuit is formed in said second semiconductor layer.

Claim 31 (New): A semiconductor device according to claim 29, wherein an area of said second semiconductor layer is larger than a sum of the areas of said plurality of first semiconductor layers.

Claim 32 (New): A semiconductor device according to claim 29, wherein said second semiconductor layer is deposited by epitaxial growth.